

STARPOWER

SEMICONDUCTOR

IGBT

GD10PUX65F1S_B22

650V/10A in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

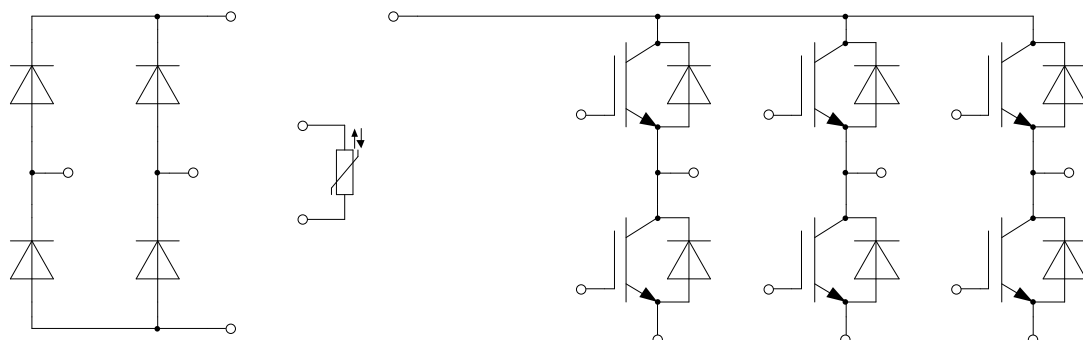
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 6 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology
- Pre-applied phase change material

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	20	A
P_D	Maximum Power Dissipation @ $T_{vj}=175^{\circ}\text{C}$	87	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	10	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

Diode-rectifier

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_O	Average Output Current 50Hz/60Hz,sine wave	10	A
I_{FSM}	Surge Forward Current $t_p=10\text{ms}$ @ $T_{vj}=25^{\circ}\text{C}$	250	A
	@ $T_{vj}=150^{\circ}\text{C}$	220	
I^2t	I^2t -value, $t_p=10\text{ms}$ @ $T_{vj}=25^{\circ}\text{C}$	312	A^2s
	@ $T_{vj}=150^{\circ}\text{C}$	242	

Module

Symbol	Description	Value	Unit
T_{vjmax}	Maximum Junction Temperature(inverter,brake)	175	$^{\circ}\text{C}$
	Maximum Junction Temperature (rectifier)	150	
T_{vjop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_{vj}=25^{\circ}\text{C}$		1.45	1.90	V
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_{vj}=125^{\circ}\text{C}$		1.60		
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_{vj}=150^{\circ}\text{C}$		1.70		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.16\text{mA}, V_{CE}=V_{GE}, T_{vj}=25^{\circ}\text{C}$	5.1	5.8	6.5	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		1.16		nF
C_{res}	Reverse Transfer Capacitance			0.02		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.07		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=10\text{A}, R_G=27\Omega, V_{GE}=\pm 15\text{V}, L_S=24\text{nH}, T_{vj}=25^{\circ}\text{C}$		10		ns
t_r	Rise Time			13		ns
$t_{d(off)}$	Turn-Off Delay Time			59		ns
t_f	Fall Time			126		ns
E_{on}	Turn-On Switching Loss			0.16		mJ
E_{off}	Turn-Off Switching Loss			0.14		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=10\text{A}, R_G=27\Omega, V_{GE}=\pm 15\text{V}, L_S=24\text{nH}, T_{vj}=125^{\circ}\text{C}$		8		ns
t_r	Rise Time			14		ns
$t_{d(off)}$	Turn-Off Delay Time			70		ns
t_f	Fall Time			171		ns
E_{on}	Turn-On Switching Loss			0.22		mJ
E_{off}	Turn-Off Switching Loss			0.20		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=10\text{A}, R_G=27\Omega, V_{GE}=\pm 15\text{V}, L_S=24\text{nH}, T_{vj}=150^{\circ}\text{C}$		7		ns
t_r	Rise Time			16		ns
$t_{d(off)}$	Turn-Off Delay Time			71		ns
t_f	Fall Time			171		ns
E_{on}	Turn-On Switching Loss			0.24		mJ
E_{off}	Turn-Off Switching Loss			0.21		mJ
I_{SC}	SC Data	$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_{vj}=150^{\circ}\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		50		A

Diode-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_C=10\text{A}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$		1.60	2.05	V
		$I_C=10\text{A}, V_{GE}=0\text{V}, T_{vj}=125^{\circ}\text{C}$		1.55		
		$I_C=10\text{A}, V_{GE}=0\text{V}, T_{vj}=150^{\circ}\text{C}$		1.50		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=10\text{A},$ $-di/dt=1500\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_s=24\text{nH}, T_{vj}=25^{\circ}\text{C}$		0.20		μC
I_{RM}	Peak Reverse Recovery Current			10.5		A
E_{rec}	Reverse Recovery Energy			0.04		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=10\text{A},$ $-di/dt=1500\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_s=24\text{nH}, T_{vj}=125^{\circ}\text{C}$		0.45		μC
I_{RM}	Peak Reverse Recovery Current			11.0		A
E_{rec}	Reverse Recovery Energy			0.10		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=10\text{A},$ $-di/dt=1500\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $L_s=24\text{nH}, T_{vj}=150^{\circ}\text{C}$		0.55		μC
I_{RM}	Peak Reverse Recovery Current			11.0		A
E_{rec}	Reverse Recovery Energy			0.11		mJ

Diode-rectifier Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=10\text{A}, T_{vj}=150^{\circ}\text{C}$		0.90		V
I_R	Reverse Current	$T_{vj}=150^{\circ}\text{C}, V_R=1600\text{V}$			3.0	mA

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			22.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=1486.1\Omega$	-5		5	%
P_{25}	Power Dissipation				200	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		4000		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case (per IGBT-inverter)		1.717	1.889	K/W
	Junction-to-Case (per Diode-inverter)		2.569	2.826	
	Junction-to-Case (per Diode-rectifier)		1.266	1.393	
R_{thCH}	Case-to-Heatsink (per IGBT-inverter)		0.309		K/W
	Case-to-Heatsink (per Diode-inverter)		0.462		
	Case-to-Heatsink (per Diode-rectifier)		0.228		
	Case-to-Sink (per Module)		0.020		
M	Mounting Torque, Screw M4	2.0		2.2	N.m
G	Weight of Module		26		g

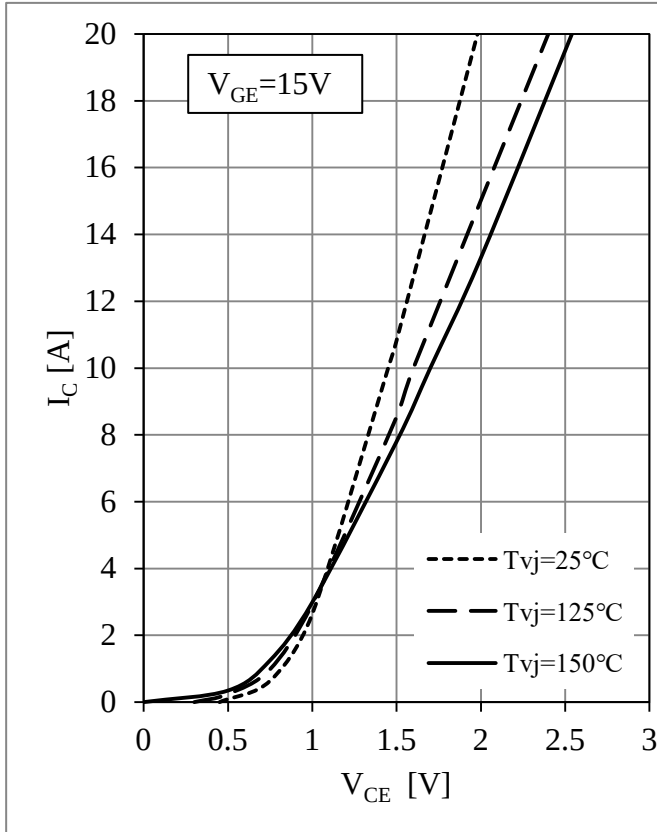


Fig 1. IGBT-inverter Output Characteristics

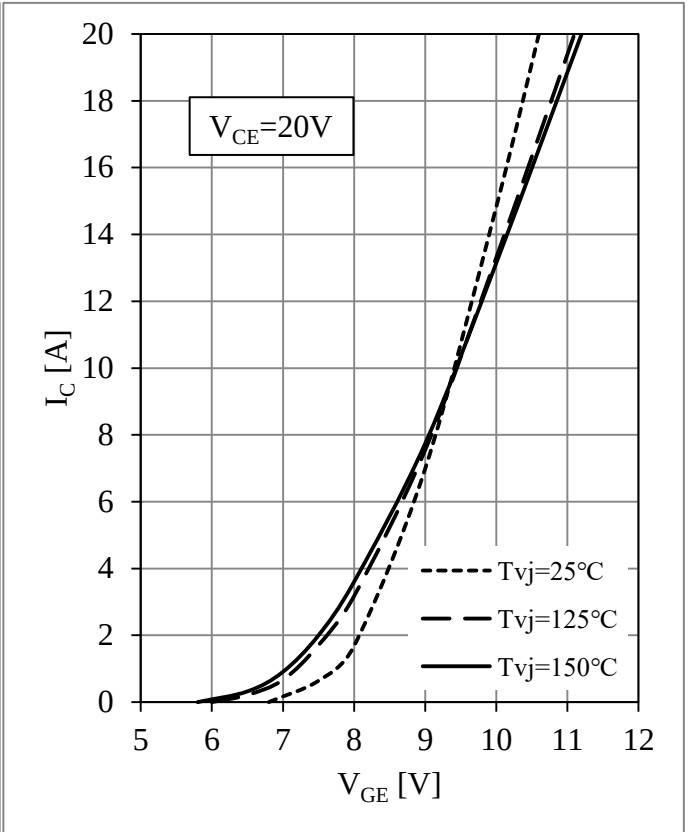
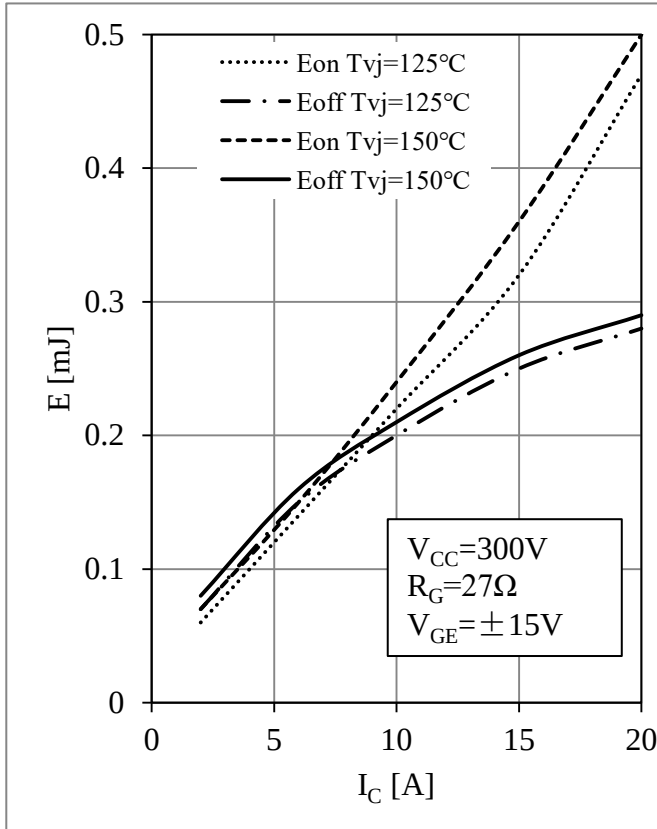
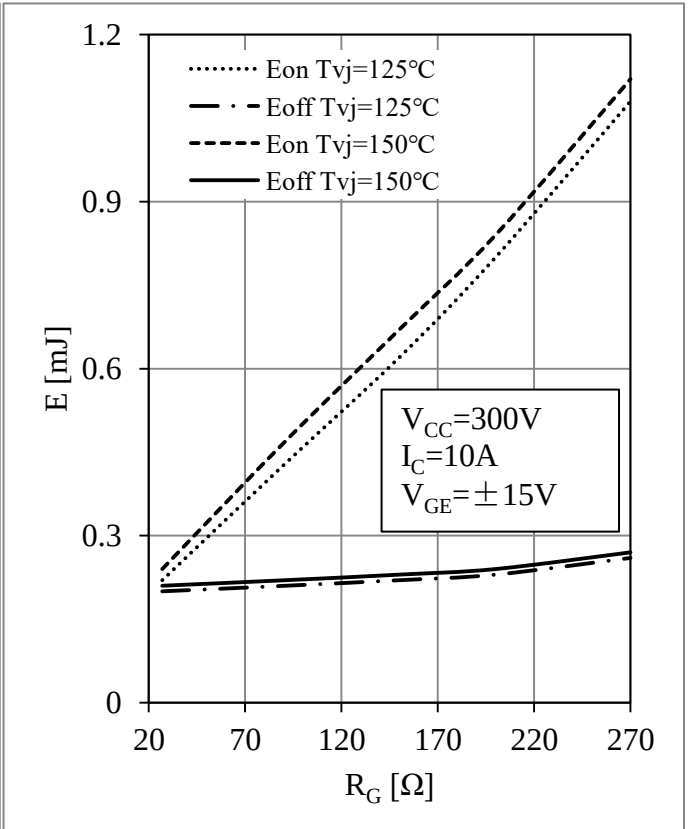


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs. I_C Fig 4. IGBT-inverter Switching Loss vs. R_G

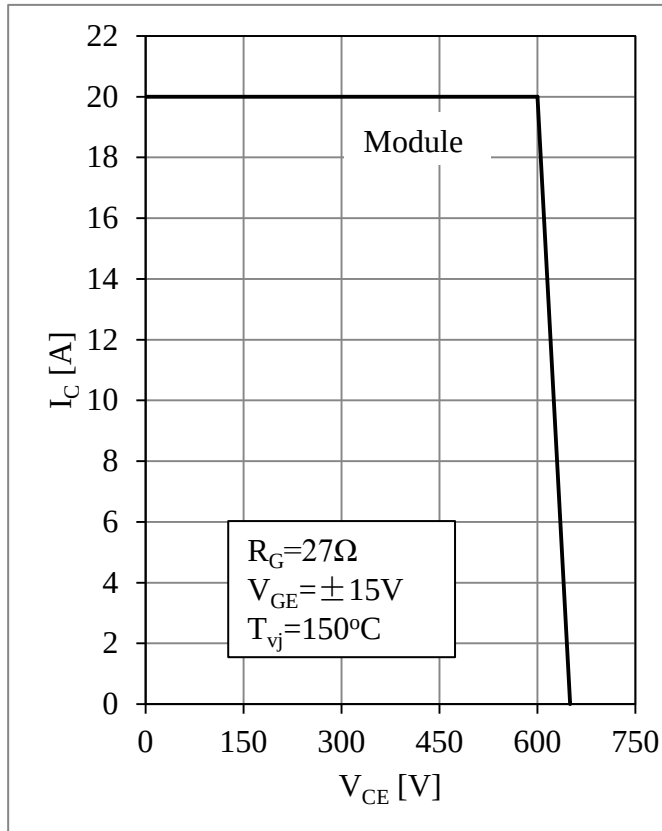


Fig 5. IGBT-inverter RBSOA

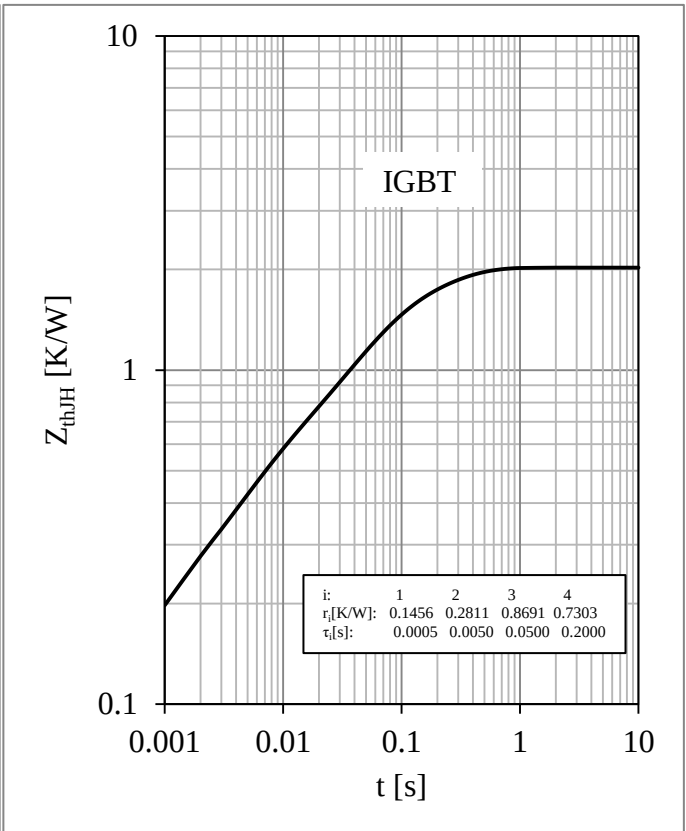


Fig 6. IGBT-inverter Transient Thermal Impedance

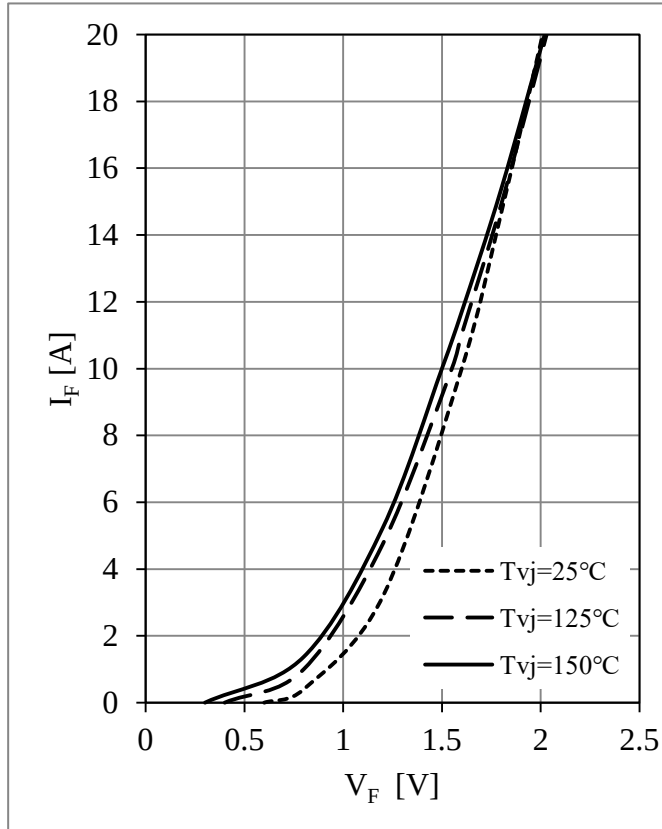
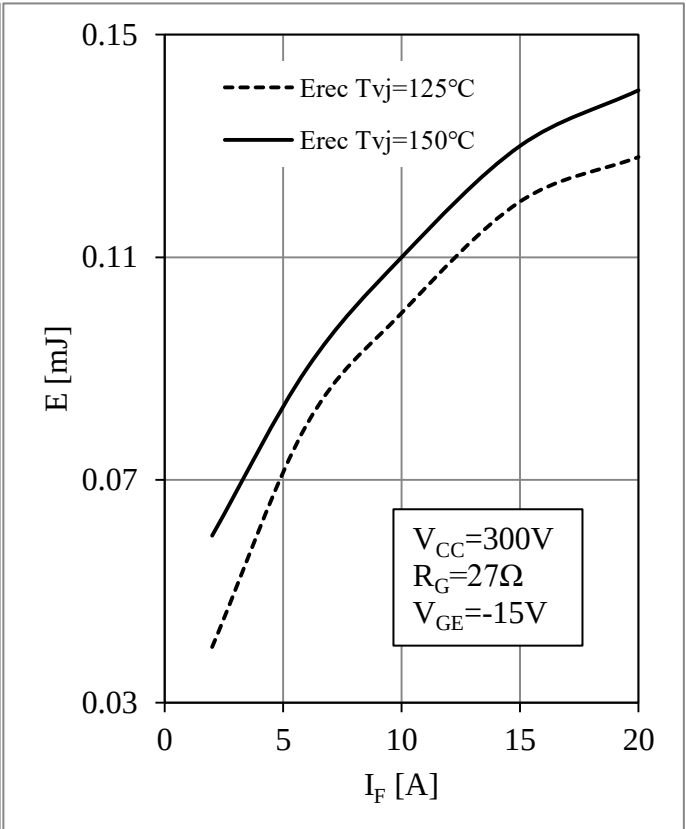


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs. I_F

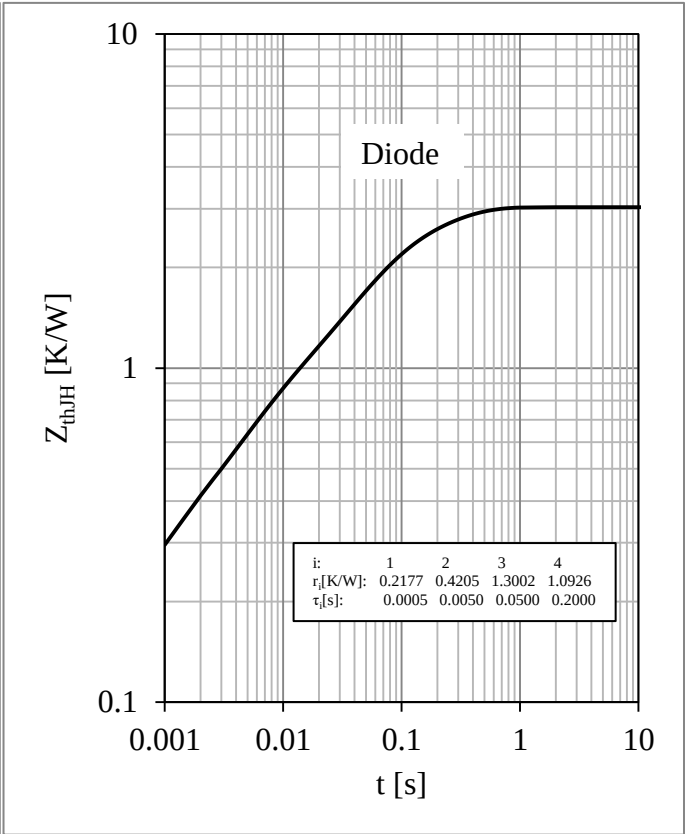
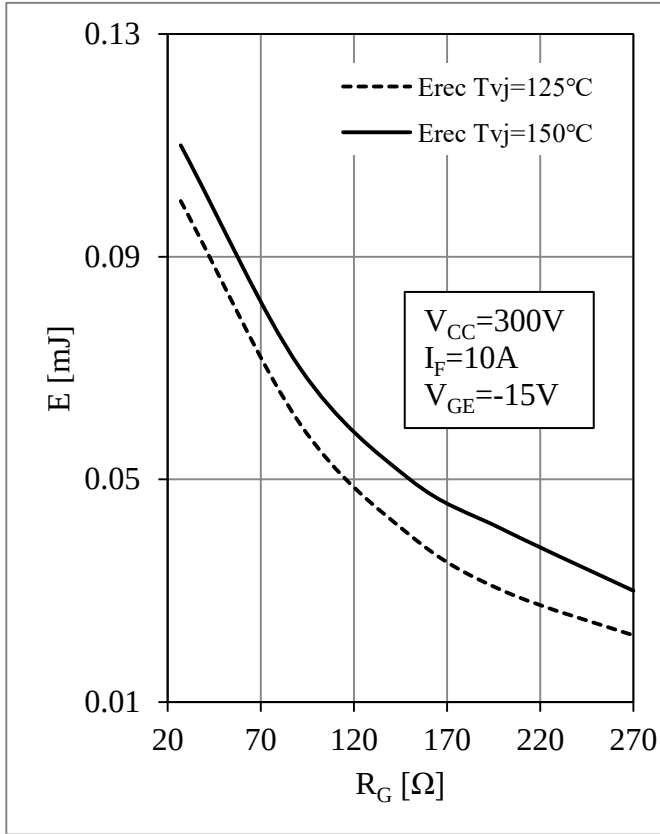
Fig 9. Diode-inverter Switching Loss vs. R_G

Fig 10. Diode-inverter Transient Thermal Impedance

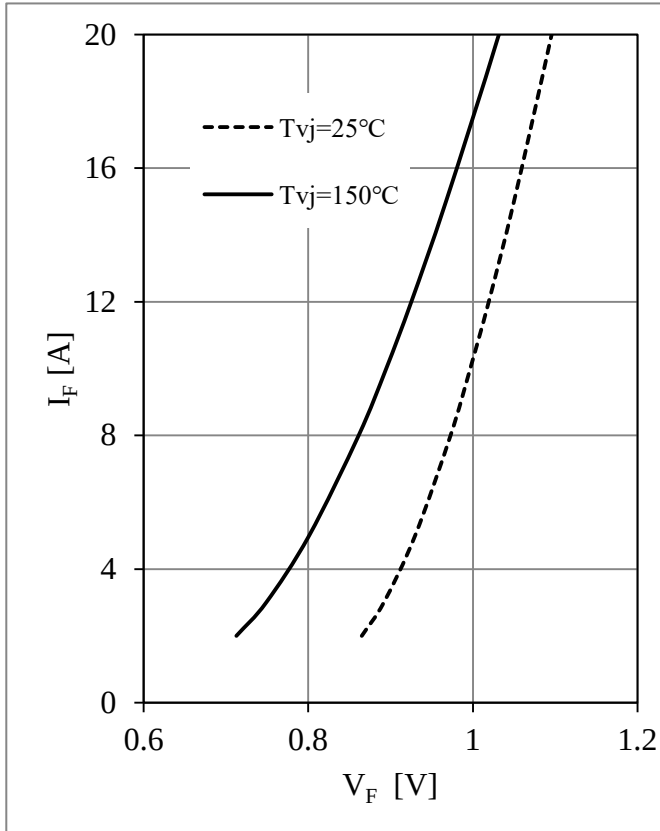


Fig 11. Diode-rectifier Forward Characteristics

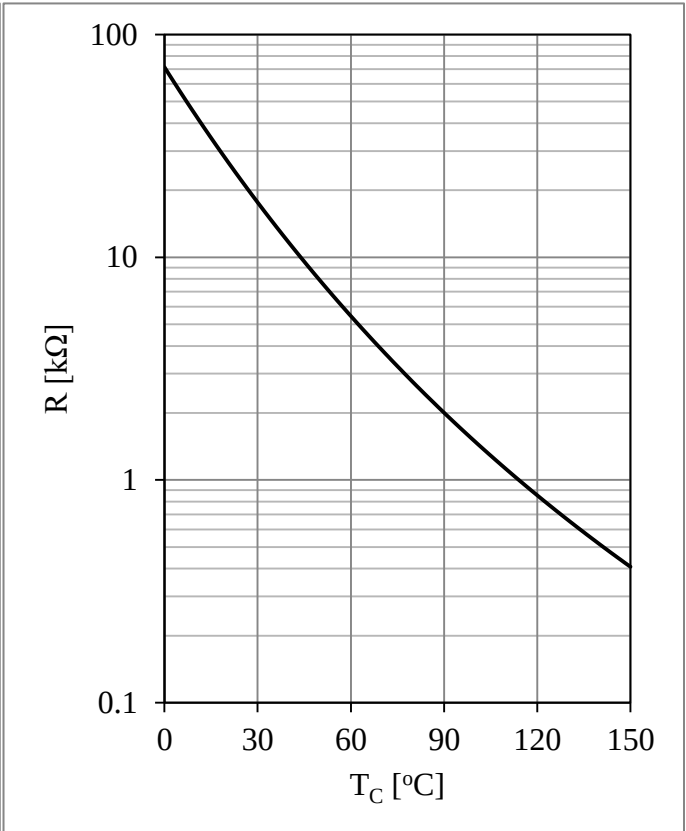
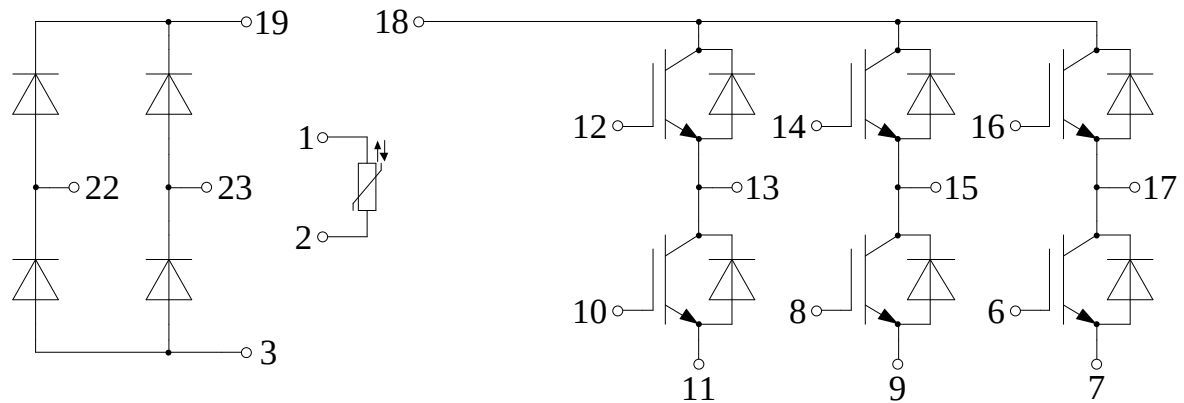


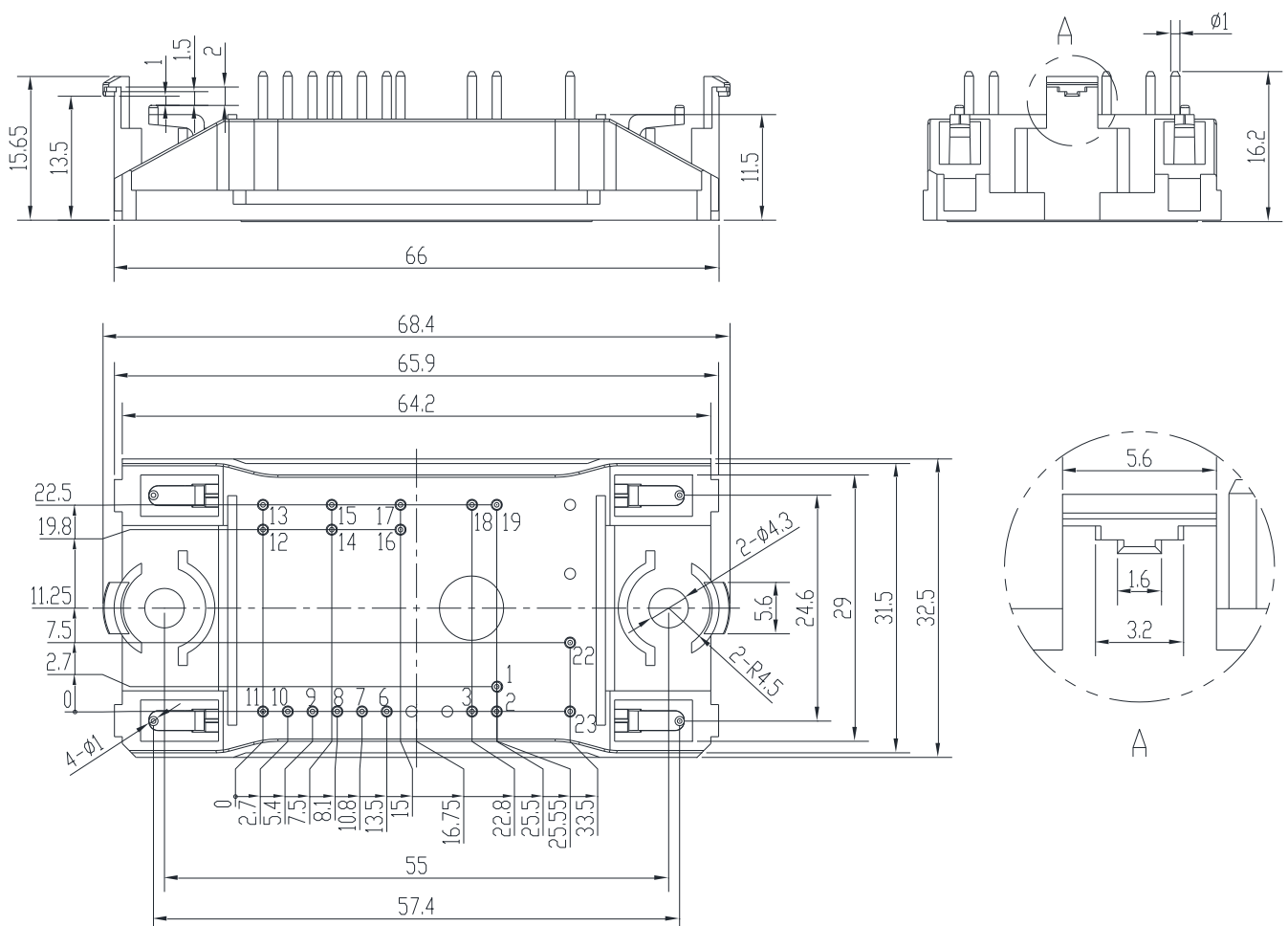
Fig 12. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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